

Ordering number:ENN6460

P-Channel Silicon MOSFET



**MCH6605**

**Ultrahigh-Speed Switching Applications**

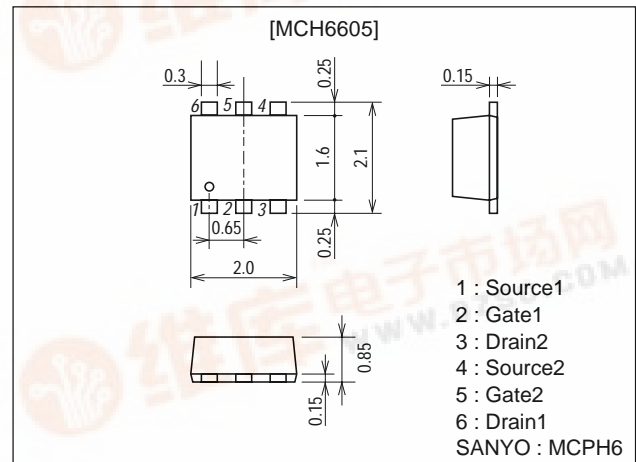
**Features**

- Low ON resistance.
- Ultrahigh-speed switching.
- 4V drive.
- Composite type with 2 MOSFETs contained in one package, facilitating high-density mounting.

**Package Dimensions**

unit:mm

2173



**Specifications**

**Absolute Maximum Ratings** at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DS</sub>		-50	V
Gate-to-Source Voltage	V <sub>GS</sub>		±20	V
Drain Current (DC)	I <sub>D</sub>		-0.14	A
Drain Current (pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-0.56	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (900mm²×0.8mm) 1unit	0.8	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

**Electrical Characteristics** at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0	-50			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-50V, V <sub>GS</sub> =0			-10	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-100μA	-1		-2.5	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-40mA	50	70		mS
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =-40mA, V <sub>GS</sub> =-10V		17	22	Ω
	R <sub>DS(on)2</sub>	I <sub>D</sub> =-20mA, V <sub>GS</sub> =-4V		23	32	Ω
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-10V, f=1MHz		6.2		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =-10V, f=1MHz		4.0		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> =-10V, f=1MHz		1.3		pF

Marking : FE

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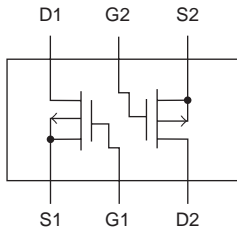


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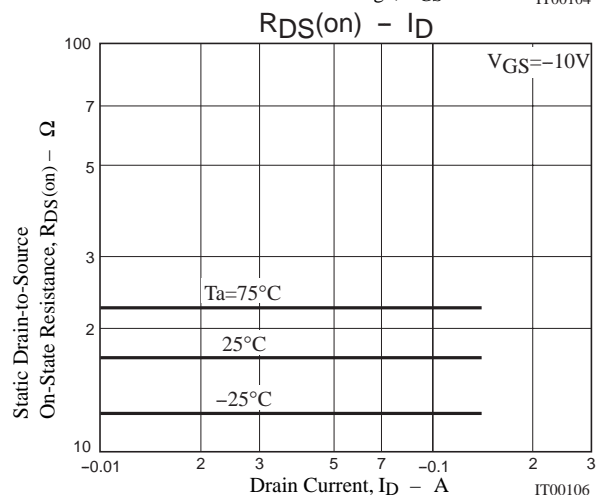
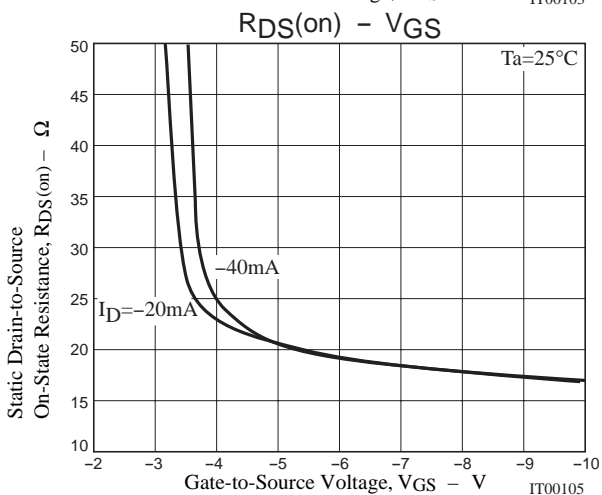
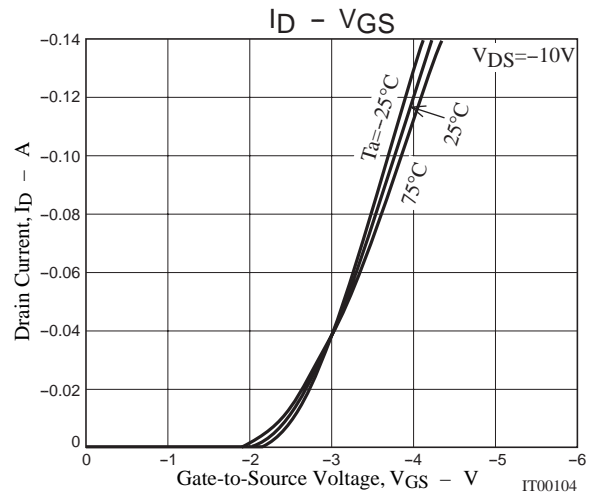
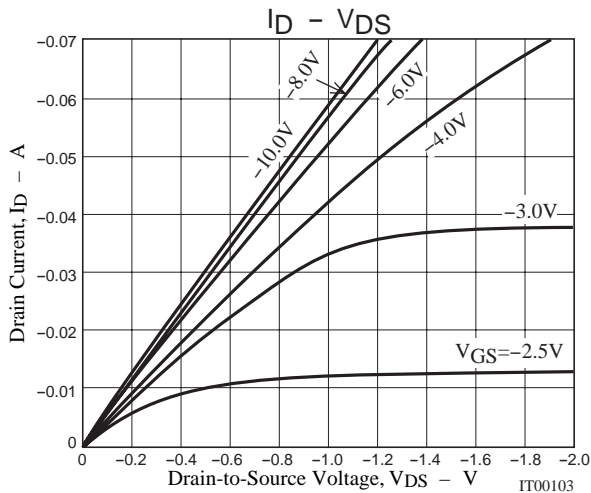
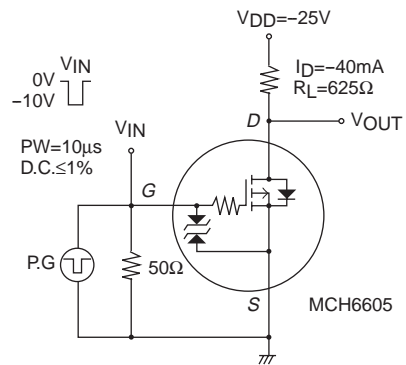
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		13		ns
Rise Time	$t_r$	See specified Test Circuit		10		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		100		ns
Fall Time	$t_f$	See specified Test Circuit		150		ns
Total Gate Charge	Qg	$V_{DS}=-10V, V_{GS}=-10V, I_D=-70mA$		1.32		nC
Gate-to-Source Charge	Qgs	$V_{DS}=-10V, V_{GS}=-10V, I_D=-70mA$		0.17		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=-10V, V_{GS}=-10V, I_D=-70mA$		0.34		nC
Diode Forward Voltage	VSD	$I_S=-70mA, V_{GS}=0$		0.85	1.2	V

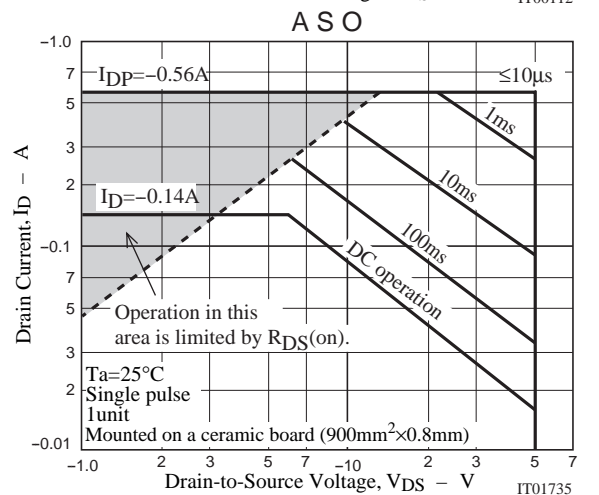
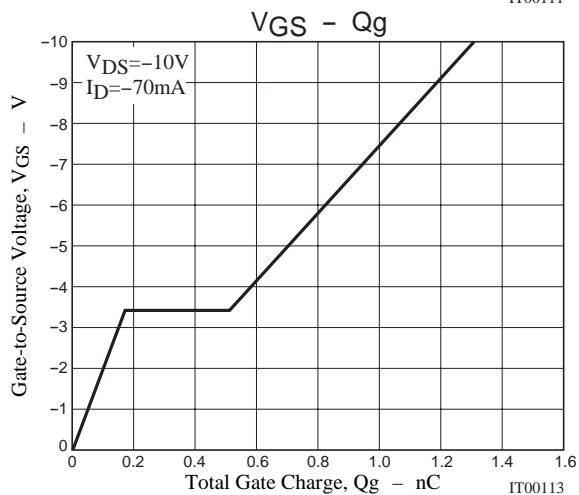
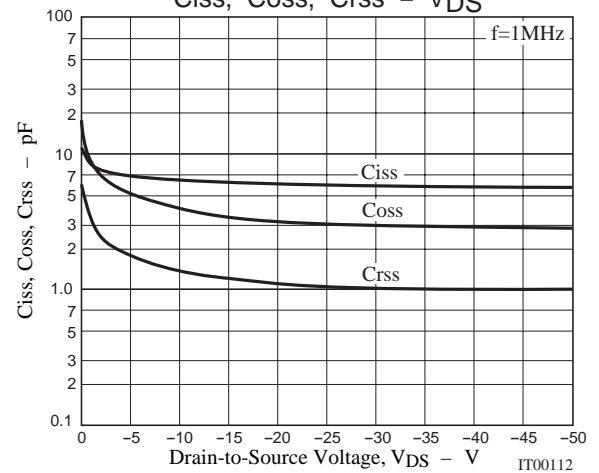
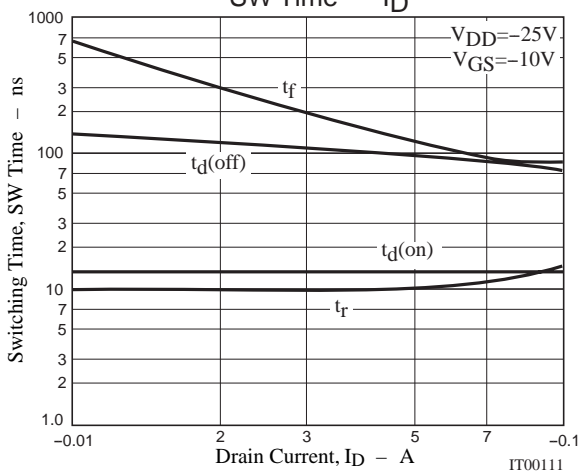
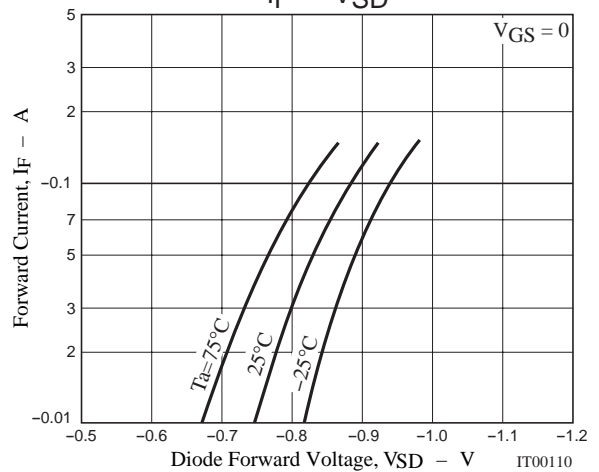
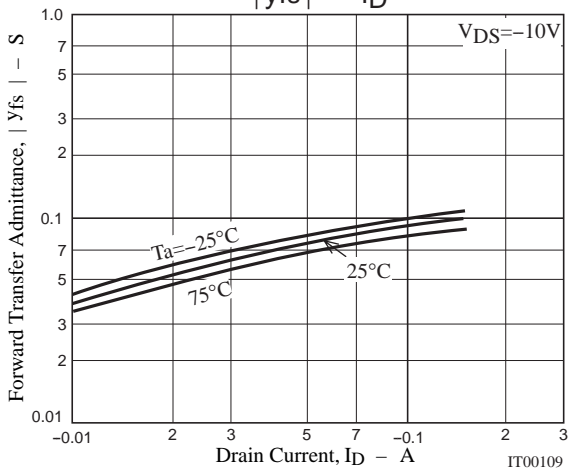
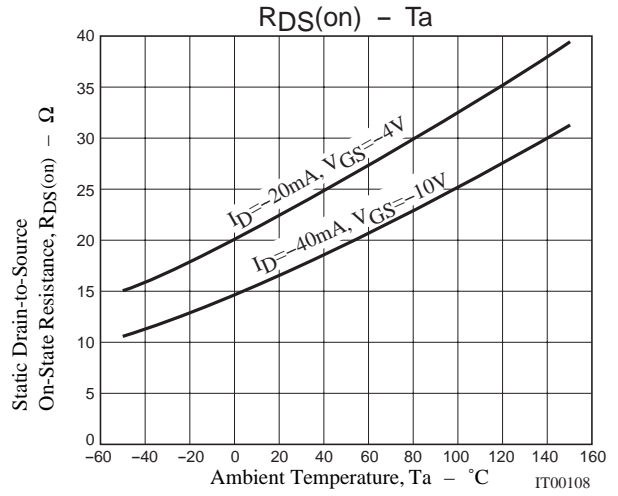
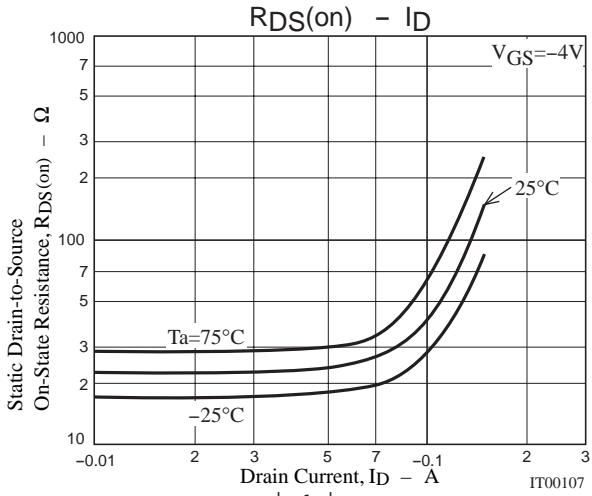
## Electrical Connection



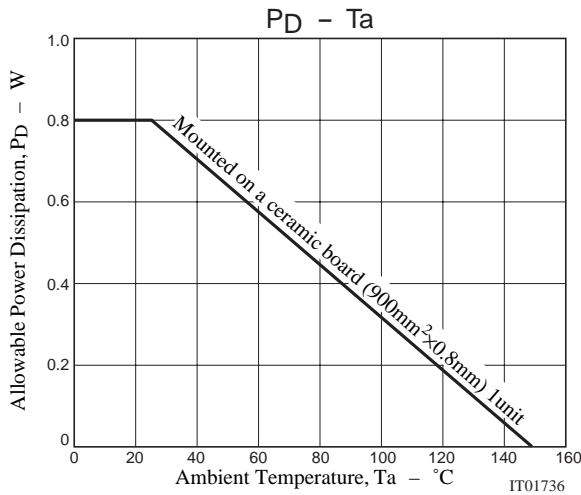
## Switching Time Test Circuit



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